

100mA 40V(0.35mm)

### Chip Information

Chip Size	0.35 x 0.35mm
Pad Size	0.23 x 0.23mm
Chip Quantity	90246 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

### MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	45	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	100	mA	
Peak Forward Surge Current	IFSM	1	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

### ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.600	0.570	0.500	V	IF=100mA Ta=25degC
	VF2	0.450	0.430	0.350	V	IF=10mA Ta=25degC
	VF3	0.340	0.330	0.285	V	IF=1mA Ta=25degC
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	1	0.2	0.06	uA	VR=10V Ta=25degC
	IR2	5	2	0.25	uA	VR=40V Ta=25degC
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	45	49	62	V	IR=10uA
Junction Capacitance	Cj			4	pF	V=10V,f=1MHz
Reverse Recovery Time	trr				nS	

### Ordering Information

Chip Type	Chip Thickness	Back Metal
XHZ055	180 +/- 20um	Au(For Eutectic)
XHZ057	150 +/- 20um	Au(For Eutectic)
XHZ056	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:

Designed For RB500V-40,RB420D,RB480K